



40V N-Channel Enhancement Mode MOSFET

Voltage

40 V

Current

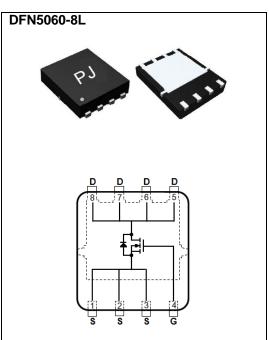
50A

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@20A<11m\Omega$
- R_{DS(ON)}, V_{GS}@4.5V, I_D@10A<15mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20		
Continuous Drain Current	T _C =25°C	l _D	50	A	
	T _C =100°C		31.5		
Pulsed Drain Current ^(Note 1)	T _C =25°C	I _{DM}	120		
Power Dissipation	T _C =25°C	Po	54	10/	
	T _C =100°C		21.6	W	
Continuous Drain Current	T _A =25°C	I _D	9.6	Α	
	T _A =70°C		7.6	Α	
Power Dissipation	T _A =25°C	Po	2.0	W	
	T _A =70°C		1.3		
Single Pulse Avalanche Energy(Note 6)		E _{AS}	62	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{ heta JC}$	2.3	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS} V _{GS} =0V,I _D =250uA		40	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $V_{DS}=250$ uA		1.7	2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =20A	-	9	11	mΩ
		V _{GS} =4.5V,I _D =10A	-	11.5	15	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =40V, V_{GS} =0V	-	-	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Q_g	V _{DS} =20V, I _D =10A, V _{GS} =4.5V ^(Note 2,3)	-	10	-	nC
Gate-Source Charge	Q_gs		-	3.5	-	
Gate-Drain Charge	Q_gd	V _{GS} =4.5V	-	3.6	-	
Input Capacitance	Ciss	\/ 20\/ \/ 0\/	-	1040	-	pF
Output Capacitance	Coss	V_{DS} =20V, V_{GS} =0V, f =1.0MHZ	-	117	-	
Reverse Transfer Capacitance	Crss	I=1.0IVIDZ	-	84	-	
Turn-On Delay Time	td _(on)		-	9.4	-	
Turn-On Rise Time	t _r	$V_{DS}=20V,I_{D}=1A,$		19	-	
Turn-Off Delay Time	td _(off)	V_{GS} =10V, R_{G} =6 Ω	-	66	-	ns
Turn-Off Fall Time	t _f		-	67	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	50	А
Diode Forward Current	I _S					
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.7	1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS}=35A, V_{DD}=25V, V_{GS}=10V, Starting T_J=25°C.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

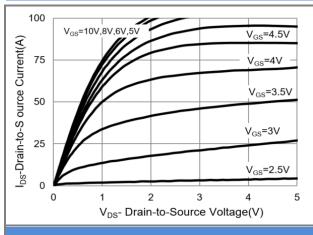


Fig.1 On-Region Characteristics

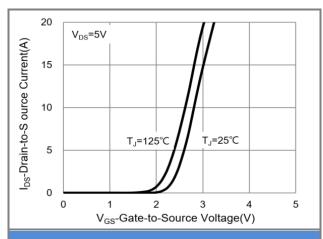


Fig.2 Transfer Characteristics

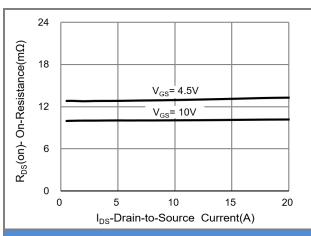


Fig.3 On-Resistance vs. Drain Current

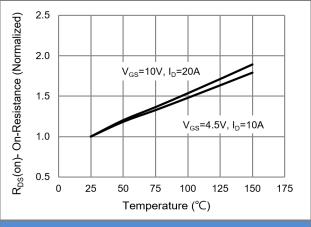


Fig.4 On-Resistance vs. Junction temperature

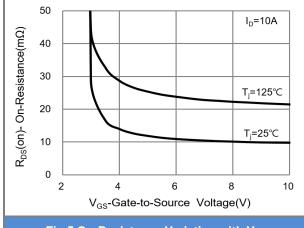


Fig.5 On-Resistance Variation with V_{GS}

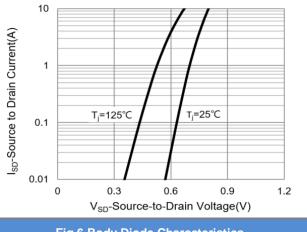


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

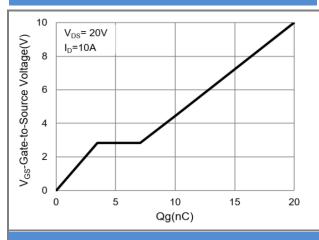


Fig.7 Gate-Charge Characteristics

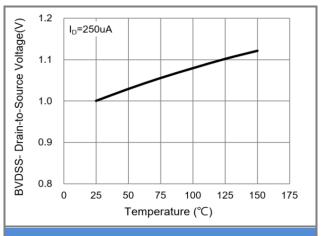


Fig.8 Breakdown Voltage Variation vs. Temperature

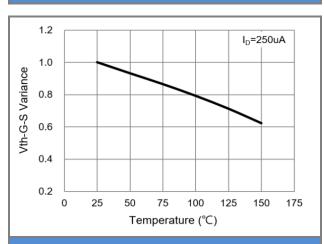


Fig.9 Threshold Voltage Variation with Temperature

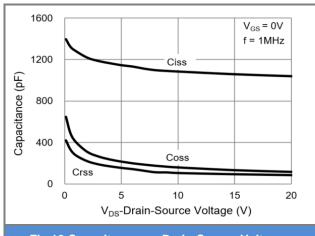


Fig.10 Capacitance vs. Drain-Source Voltage

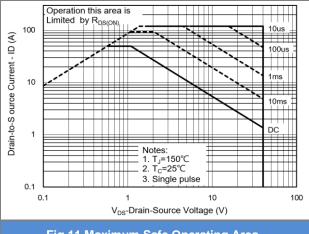


Fig.11 Maximum Safe Operating Area

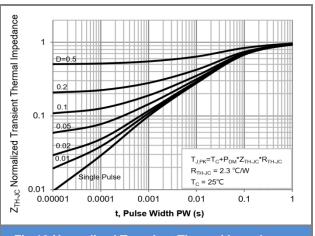


Fig.12 Normalized Transient Thermal Impedance

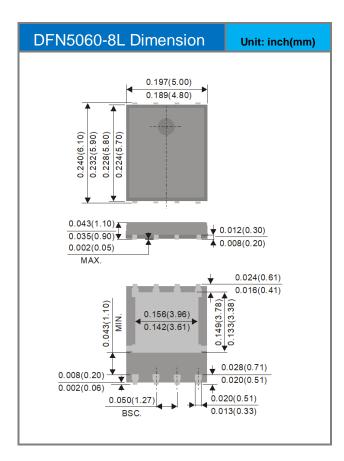


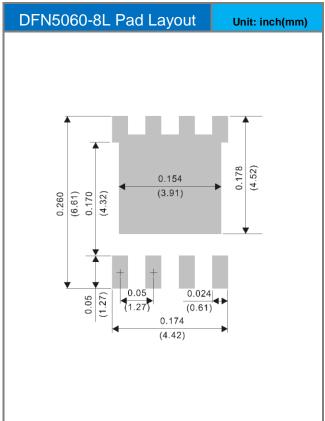


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5448_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5448	Halogen free	

Packaging Information & Mounting Pad Layout









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